

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device includes a dielectric multilayer film with a reflectance of 40% or more, formed on at least one of optical exit faces of a laser chip, wherein the dielectric multilayer film includes a dielectric film of tantalum oxide (Ta_2O_5) and another dielectric film of dielectric oxide, such as aluminum oxide (Al_2O_3), silicon oxide (SiO_2), the tantalum oxide film having an optical absorption coefficient smaller than that of silicon (Si) film and thermal stability in emission superior to that of titanium oxide (TiO_2) film, thereby remarkably improving the COD degradation level.